MOSFET - Single P-Channel, Small Signal, XDFN3, 0.62 x 0.42 x 0.4 mm

-20 V, -127 mA

Features

- Low Profile Ultra Small Package, XDFN3 (0.62 x 0.42 x 0.4 mm) for Extremely Space–Constrained Applications
- -1.5 V Gate Drive
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Small Signal Load Switch
- High Speed Interfacing
- Level Shift

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	20	V
Gate-to-Source Voltage			V _{GS}	±8	V
Continuous Drain Current (Note 1)	Steady	T _A = 25°C	I _D	-127	mA
	State	T _A = 85°C		-91	
	t ≤ 5 s	T _A = 25°C		-146	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	125	mW
	t ≤ 5 s			166	
Pulsed Drain Current	t _p = 10 μs		I _{DM}	-488	mA
Operating Junction and Storage Temperature			T _J , T _{STG}	–55 to 150	°C
Source Current (Body Diode) (Note 2)			Is	200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Surface-mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.
- 2. Pulse Test: pulse width $\leq 300~\mu s, \, duty \; cycle \leq 2\%$

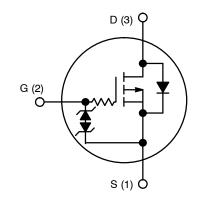


ON Semiconductor®

www.onsemi.com

V _{(BR)DSS}	R _{DS(on)} MAX I _D Max	
	5.0 Ω @ -4.5 V	
	5.5 Ω @ -3.3 V	
-20 V	6.0 Ω @ -2.5 V	–127 mA
	7.0 Ω @ –1.8 V	
	10 Ω @ -1.5 V	

P-CHANNEL MOSFET



MARKING DIAGRAM





XDFN3 CASE 711BH

F = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NTNS5K0P021ZTCG	XDFN3 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit	
Junction-to-Ambient - Steady State (Note 3)	$R_{\theta JA}$	998	- °C/W	
Junction-to-Ambient - t ≤ 5 s (Note 3)	$R_{\theta JA}$	751		

^{3.} Surface–mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise stated)

Parameter	Symbol	Test Condition	1	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•				•		
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = -25$	0 μΑ	-20			٧
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 \text{ V}, V_{DS} = -5 \text{ V}$	T _J = 25°C			-50	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 \text{ V}, V_{DS} = -16 \text{ V}$	T _J = 25°C			-100	nA
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 1$	5 V			±100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}$, $I_D = -2$	50 μΑ	-0.4		-1.0	V
		$V_{GS} = -4.5 \text{ V}, I_D = -1$	00 mA		2.1	5.0	
		$V_{GS} = -3.3 \text{ V}, I_D = -100 \text{ mA}$			2.4	5.5	Ω
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -50 \text{ mA}$			2.7	6.0	
		$V_{GS} = -1.8 \text{ V}, I_D = -20 \text{ mA}$			3.6	7.0	
		$V_{GS} = -1.5 \text{ V}, I_D = -10 \text{ mA}$			4.2	10	
Forward Transconductance	9FS	V _{DS} = −5 V, I _D = −125 mA			0.35		S
Source-Drain Diode Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_S = -10 \text{ mA}$			-0.6	-1.0	V
CHARGES & CAPACITANCES	•				•		
Input Capacitance	C _{ISS}	$V_{GS} = 0 \text{ V}$, freq = 1 MHz, $V_{DS} = -15 \text{ V}$			12.8		
Output Capacitance	C _{OSS}				2.8		pF
Reverse Transfer Capacitance	C _{RSS}				2.0		
SWITCHING CHARACTERISTICS, VG	S = 4.5 V (Not	e 4)					
Turn-On Delay Time	t _{d(ON)}				37		
Rise Time	t _r	$V_{GS} = -4.5 \text{ V}, V_{DD} =$	–15 V,		71		
Turn-Off Delay Time	t _{d(OFF)}	$V_{GS} = -4.5 \text{ V}, V_{DD} = I_D = 200 \text{ mA}, R_G = 0.00 \text{ mA}$	2Ω		280		ns
Fall Time	t _f	1			171		1

^{4.} Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

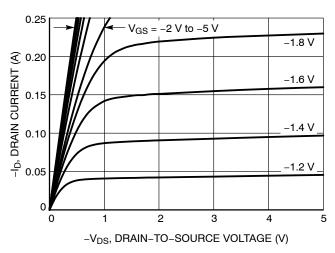
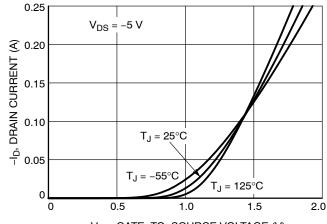


Figure 1. On-Region Characteristics



-V_{GS}, GATE-TO-SOURCE VOLTAGE (V) Figure 2. Transfer Characteristics

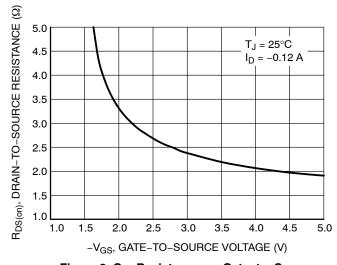


Figure 3. On-Resistance vs. Gate-to-Source Voltage

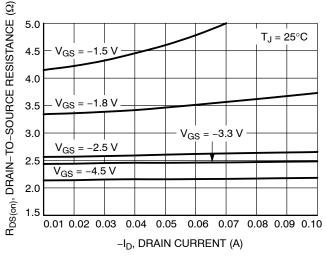


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

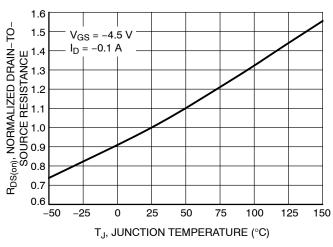


Figure 5. On–Resistance Variation with Temperature

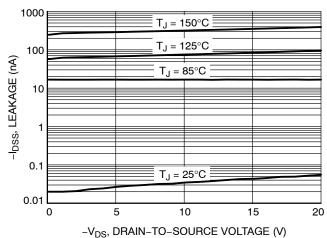


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

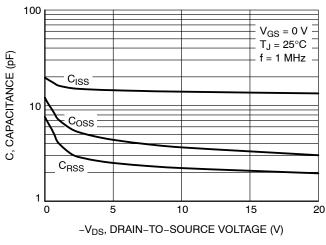


Figure 7. Capacitance Variation

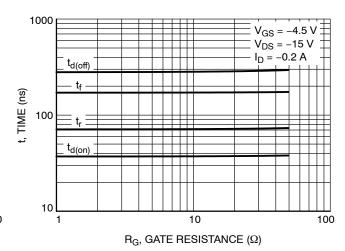


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

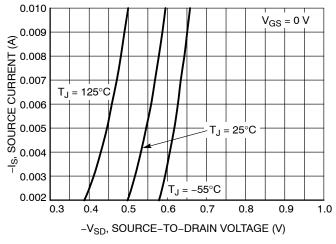


Figure 9. Diode Forward Voltage vs. Current

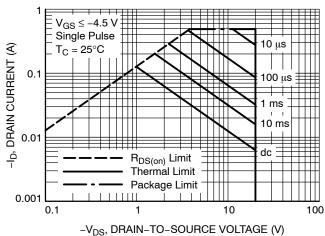


Figure 10. Maximum Rated Forward Biased Safe Operating Area

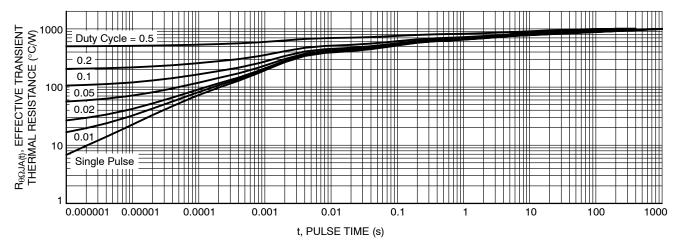
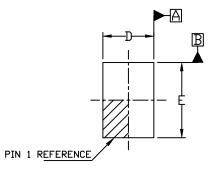


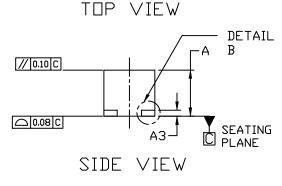
Figure 11. Thermal Response



DATE 29 APR 2018

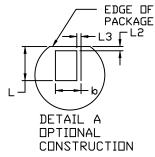






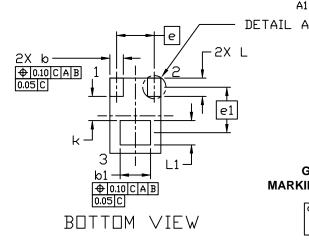
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSION 6 AND 61 APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 0.20 AND 0.25 FROM THE TERMINAL TIP.
- COPLANARITY APPLIES TO THE PLATED TERMINALS.



Γ ^{A3}	EXPOSED COPPER
	MOLDING COMPOUND
DETAIL B A1 OPTIONAL COM	NSTRUCTION

	ILIES ID IIIL I LAILD ILKIIINALS.					
MILLIMETERS						
MIN.	N□M.	MAX.				
0.33	0.38	0.43				
		0.07				
0.13 REF						
0.05	0.11	0.17				
0.20	0.25	0.30				
0.32	0.42	0.52				
0.52	0.62	0.72				
0.30 BSC						
0.38 B2C						
0.09	0.15	0.21				
0.15	0.20	0.25				
		0.03				
		0.03				
0.20 REF						
	MIN. 0.33 0.05 0.20 0.32 0.52 0.52 0.09 0.15	MIN. NIM. 0.33 0.38 0.13 REF 0.05 0.11 0.20 0.25 0.32 0.42 0.52 0.62 0.30 BSC 0.38 BSC 0.38 BSC 0.09 0.15 0.15 0.20				



GENERIC MARKING DIAGRAM*



= Specific Device Code Χ Μ = Date Code

PACKAGE DUTLINE		− 0.35
0.29		0.30
0.11		2X 0.25
2X 0.21 0.52	 	0.31 PITCH
RECON	MEN]	DED

MOUNTING FOOTPRINT

*This information is generic. Please refer	
to device data sheet for actual part	
marking. Pb-Free indicator, "G", may	
or not be present. Some products may	
not follow the Generic Marking.	

DESCRIPTION	XDFN3 0.42x0.62, 0.3P	•	PAGE 1 OF 1	
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